

Selection Guide

Part No.	Dice	Lens Type	Iv (ucd) [1] @ 10mA		Description
			Min.	Typ.	
SA10-11EWA	High Efficiency Red (GaAsP/GaP)	WHITE DIFFUSED	3000	16000	Common Anode, Rt. Hand Decimal

Note:

1. Luminous intensity/ luminous Flux: +/-15%.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	High Efficiency Red	627		nm	I _F =20mA
λ_D [1]	Dominant Wavelength	High Efficiency Red	625		nm	I _F =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	High Efficiency Red	45		nm	I _F =20mA
C	Capacitance	High Efficiency Red	15		pF	V _F =0V;f=1MHz
V _F [2]	Forward Voltage Per Segment Or (DP)	High Efficiency Red	4.0 (2.0)	5.0 (2.5)	V	I _F =20mA
I _R	Reverse Current Per Segment Or (DP)	High Efficiency Red		10 (10)	uA	V _R =10V (V _R =5V)

Notes:

1. Wavelength: +/-1nm.

2. Forward Voltage: +/-0.1V.

Absolute Maximum Ratings at TA=25°C

Parameter	High Efficiency Red	Units
Power dissipation Per Segment Or (DP)	150 (75)	mW
DC Forward Current Per Segment Or (DP)	30 (30)	mA
Peak Forward Current [1] Per Segment Or (DP)	160 (160)	mA
Reverse Voltage Per Segment Or (DP)	10 (5)	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

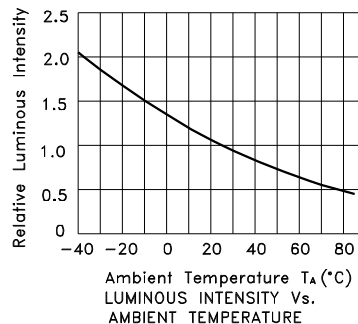
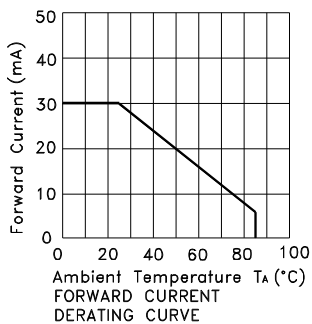
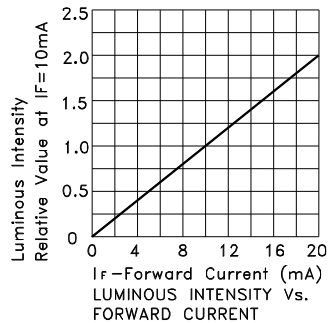
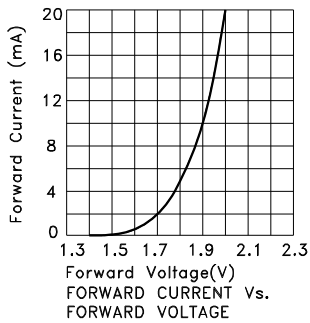
Notes:

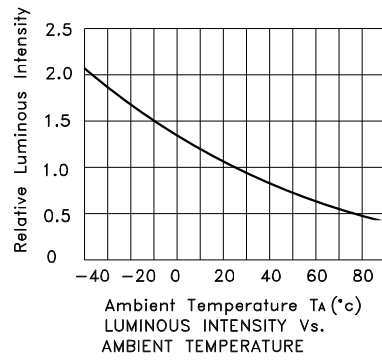
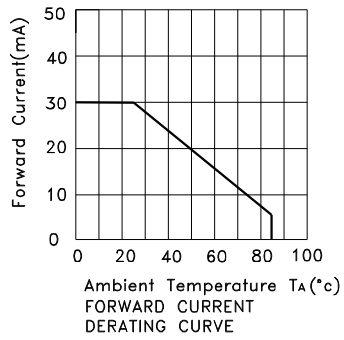
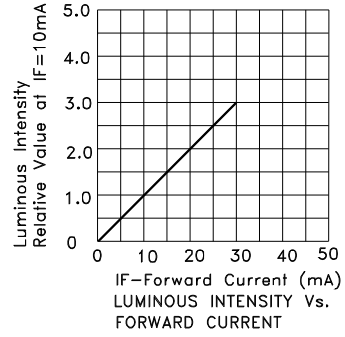
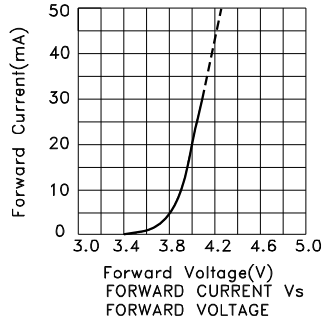
1. 1/10 Duty Cycle, 0.1ms Pulse Width.

2. 2mm below package base.



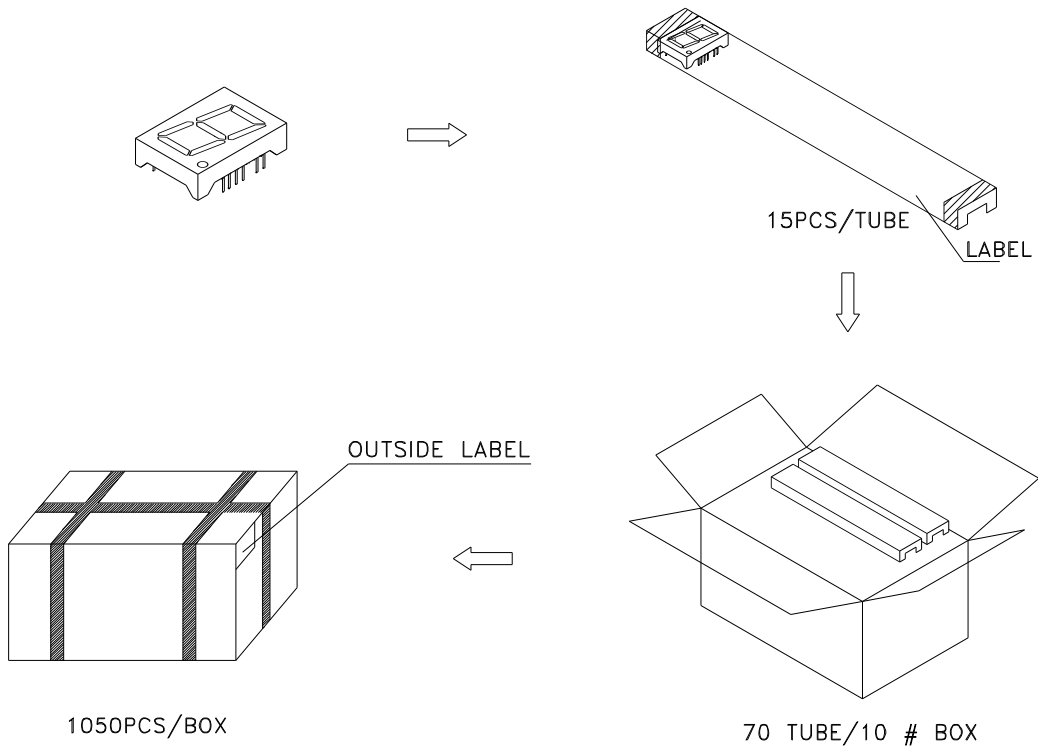
High Efficiency Red SA10-11EWA



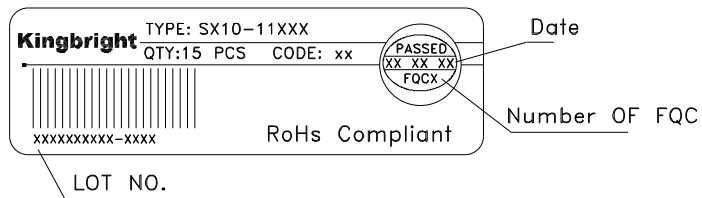


PACKING & LABEL SPECIFICATIONS

SA10-11EWA



Inside LABEL Paste On The IC-tube



Outside LABEL Paste On The Box

